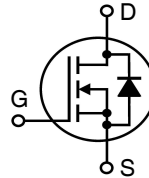


# X-Class HiPerFET™ Power MOSFET

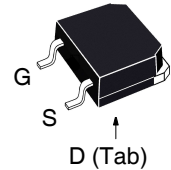
## IXFT32N100XHV IXFH32N100X IXFK32N100X

$V_{DSS} = 1000V$   
 $I_{D25} = 32A$   
 $R_{DS(on)} \leq 220m\Omega$

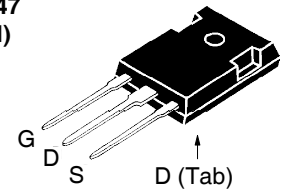
N-Channel Enhancement Mode  
Avalanche Rated



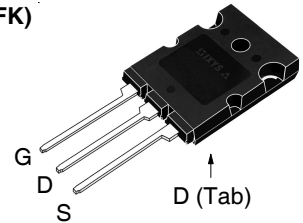
TO-268HV  
(IXFT..HV)



TO-247  
(IXFH)



TO-264  
(IXFK)



G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1000	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	32	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	64	A
$I_A$	$T_C = 25^\circ C$	16	A
$E_{AS}$	$T_C = 25^\circ C$	2	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	50	V/ns
$P_D$	$T_C = 25^\circ C$	890	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-247 & TO-264)	1.13 / 10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247	6	g
	TO-264	10	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4mA$	3.5		6.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			220 m $\Omega$

### Features

- International Standard Packages
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 16\text{A}$ , Note 1	14	23	S
$R_{Gi}$	Gate Input Resistance		0.6	$\Omega$
$C_{iss}$	} $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		4075	pF
$C_{oss}$			520	pF
$C_{rss}$			10	pF
<b>Effective Output Capacitance</b>				
$C_{o(er)}$	Energy related } $V_{GS} = 0\text{V}$		140	pF
$C_{o(tr)}$	Time related } $V_{DS} = 0.8 \cdot V_{DSS}$		585	pF
<b>Resistive Switching Times</b>				
$t_{d(on)}$	} $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		29	ns
$t_r$			12	ns
$t_{d(off)}$			80	ns
$t_f$			12	ns
$Q_{g(on)}$	} $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		130	nC
$Q_{gs}$			27	nC
$Q_{gd}$			70	nC
$R_{thJC}$				0.14 $^\circ\text{C/W}$
$R_{thCS}$	TO-247		0.21	$^\circ\text{C/W}$
	TO-264P		0.15	$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			32 A
$I_{SM}$	Repetitive, pulse Width Limited by $T_{JM}$			128 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	} $I_F = 16\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		200	ns
$Q_{RM}$			1.5	$\mu\text{C}$
$I_{RM}$			15	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

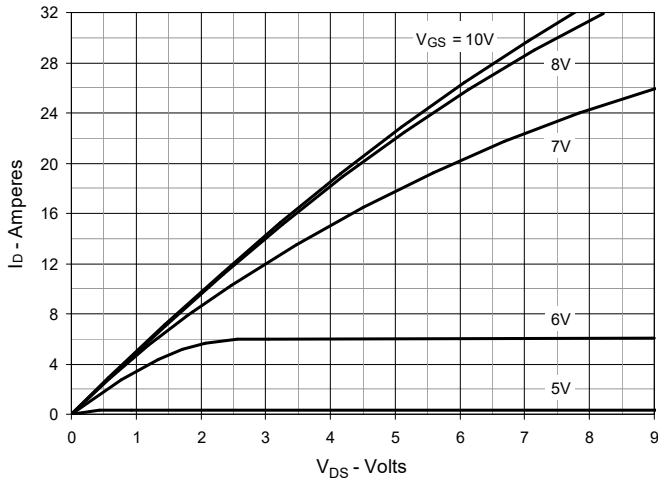


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

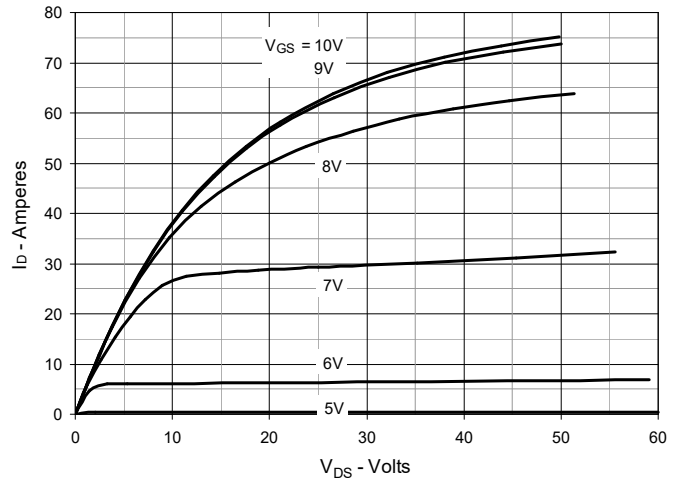


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

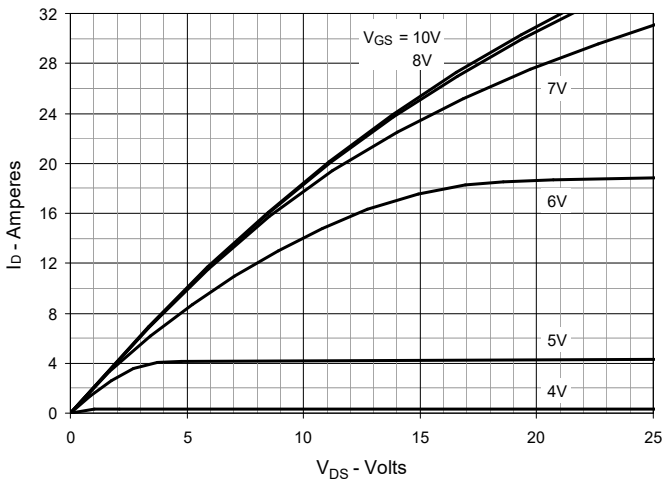


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 16\text{A}$  Value vs. Junction Temperature

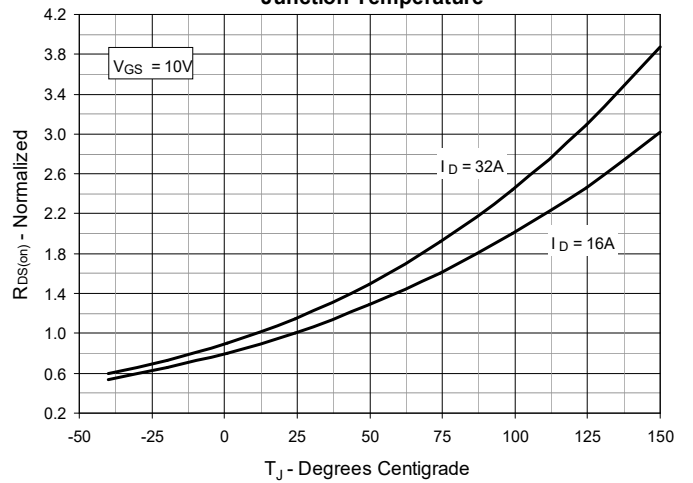


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 16\text{A}$  Value vs. Drain Current

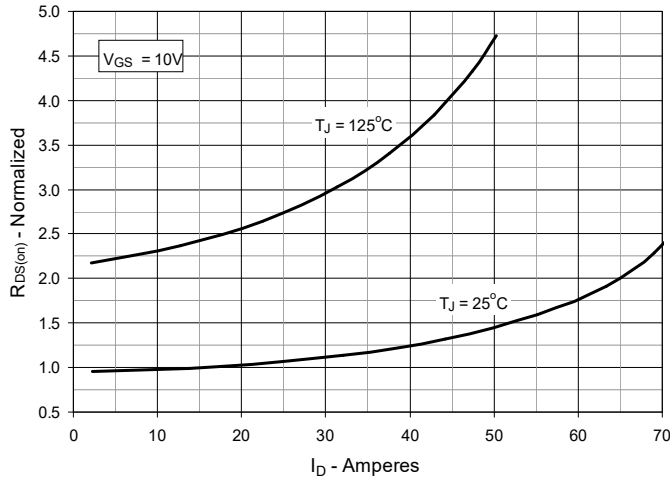
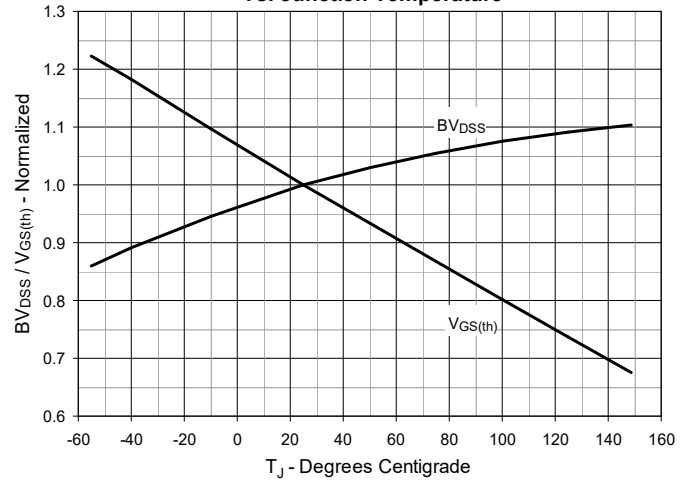


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature



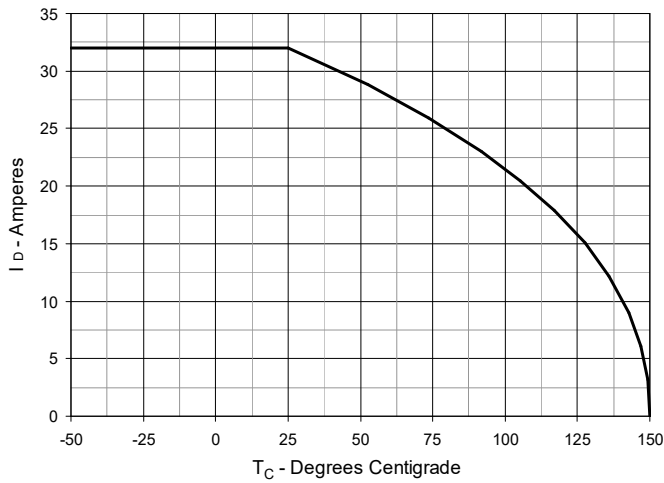
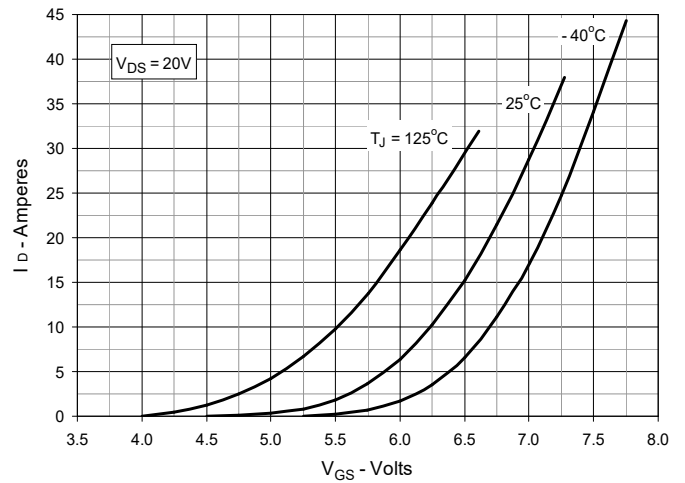
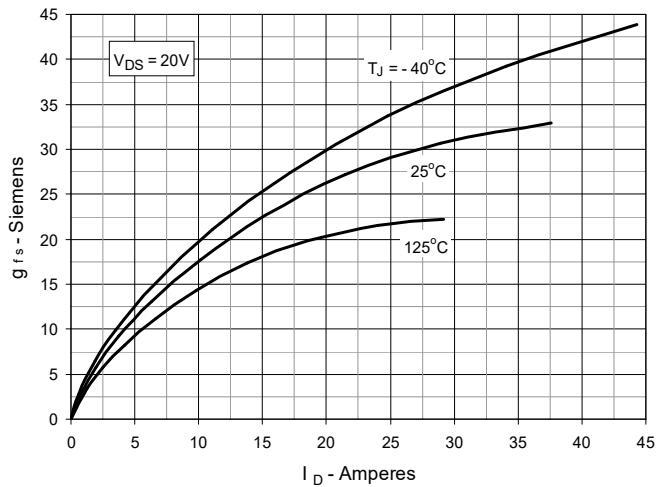
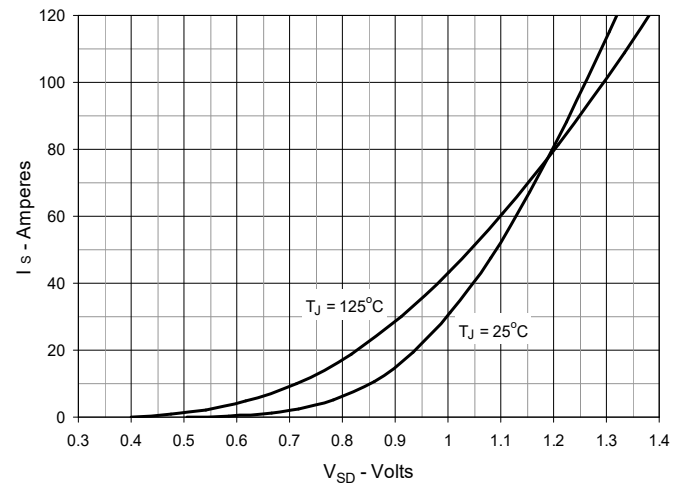
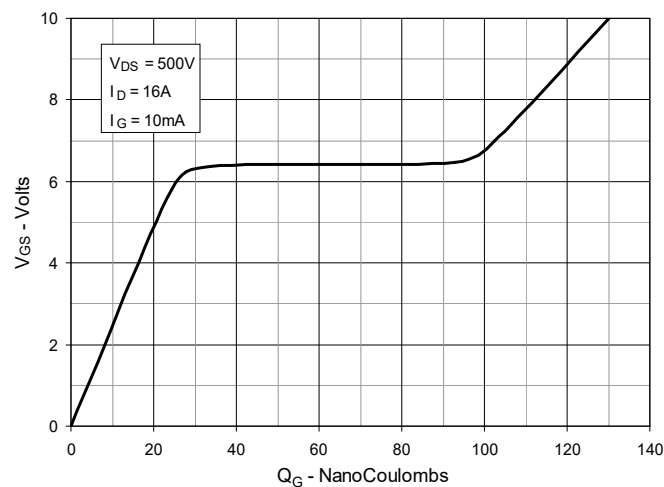
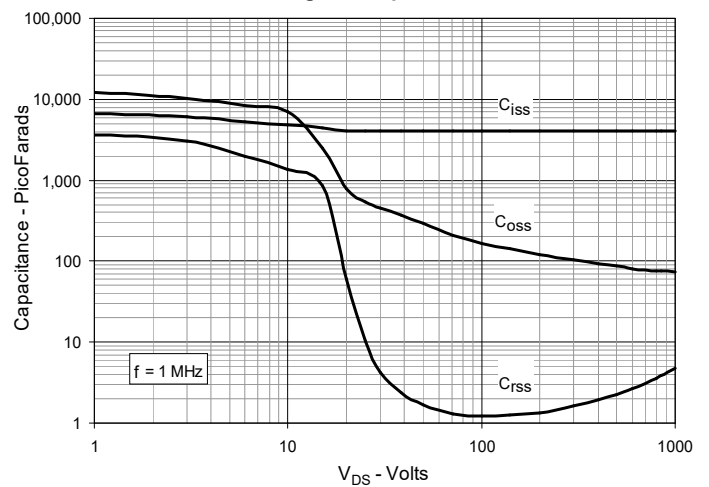
**Fig. 7. Maximum Drain Current vs. Case Temperature**

**Fig. 8. Input Admittance**

**Fig. 9. Transconductance**

**Fig. 10. Forward Voltage Drop of Intrinsic Diode**

**Fig. 11. Gate Charge**

**Fig. 12. Capacitance**


Fig. 13. Output Capacitance Stored Energy

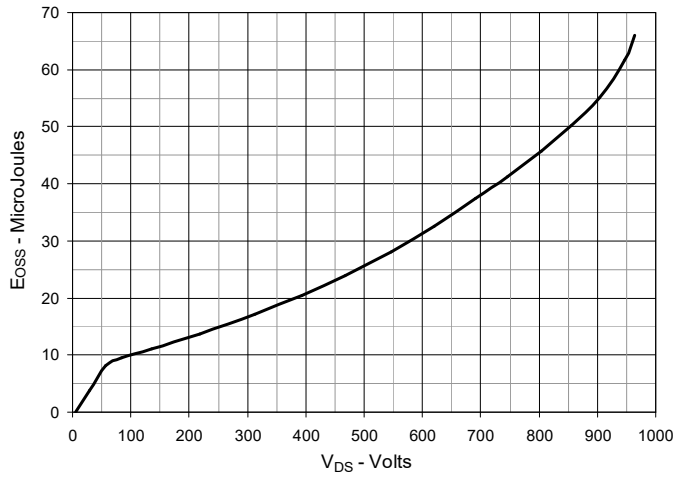


Fig. 14. Forward-Bias Safe Operating Area

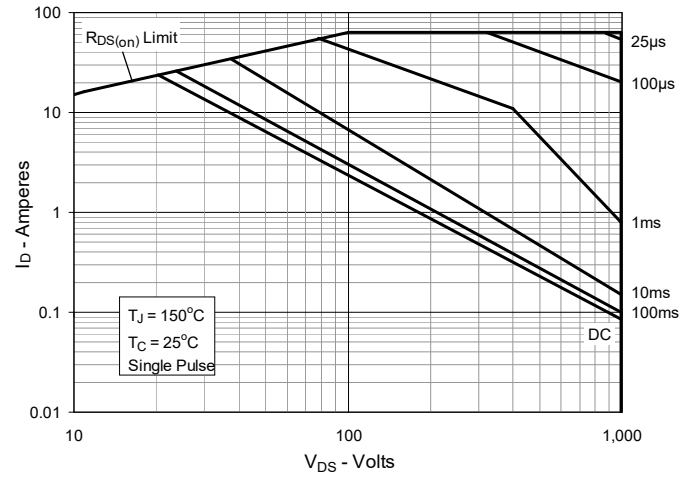
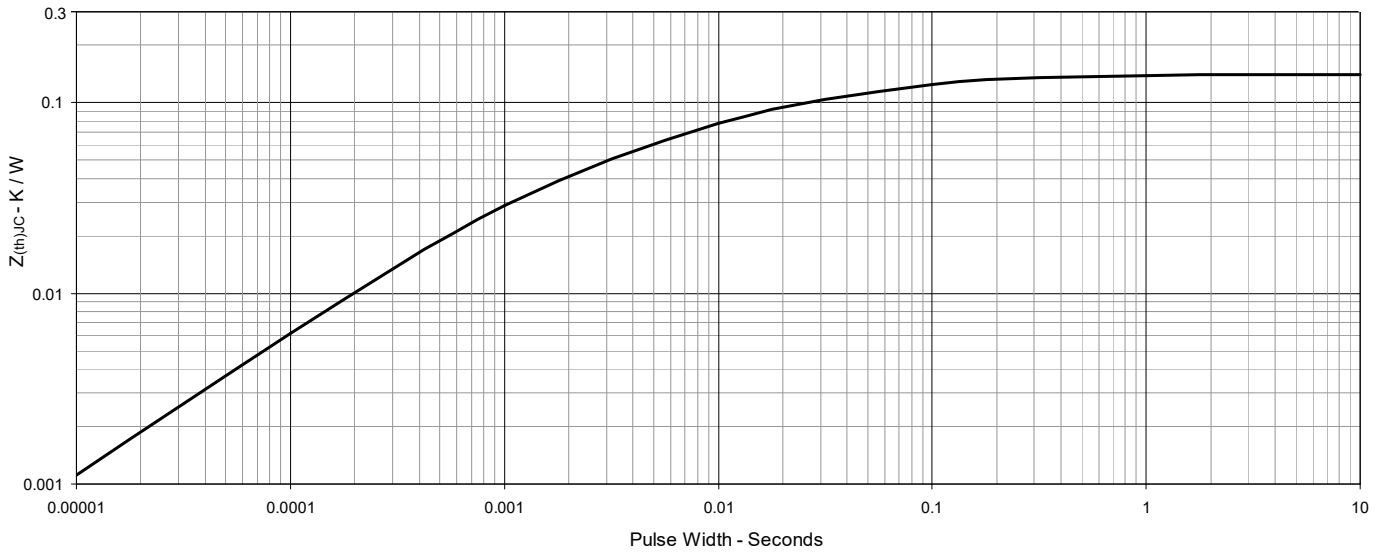
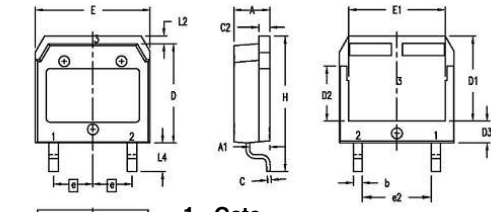


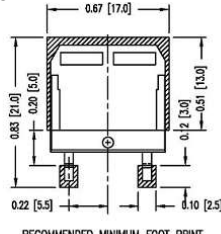
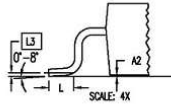
Fig. 15. Maximum Transient Thermal Impedance



### TO-268HV Outline



- 1 - Gate
- 2 - Source
- 3 - Drain



CREEPAGE DISTANCE			
DESCRIPTION	SYMBOL	MIN DISTANCE	
LEAD TO LEAD AIR CLEARANCE	e2	0.372 [9.45mm]	
LEAD TO LEAD PKG SURFACE CREEPAGE	e2	0.374 [9.50mm]	
LEAD TO BOTTOM DRAIN CREEPAGE	A1+D3	0.213 [5.40mm]	

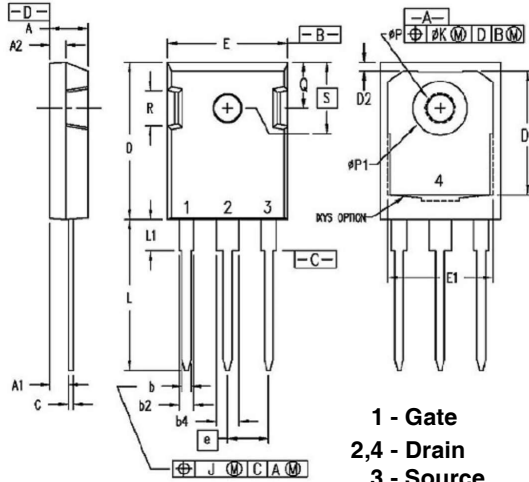
RECOMMENDED MINIMUM FOOT PRINT

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

NOTE:

1. This drawing meets all dimensions requirement of JEDEC outlines TO-268AA except L dimension.
2. All metal surface are matte pure tin plated except trimmed area.
3. [L3] is Gauge plane to measure L.
4. These dimension do not include mold flash and they will not exceed 0.005[0.13] per side.

### TO-247 Outline

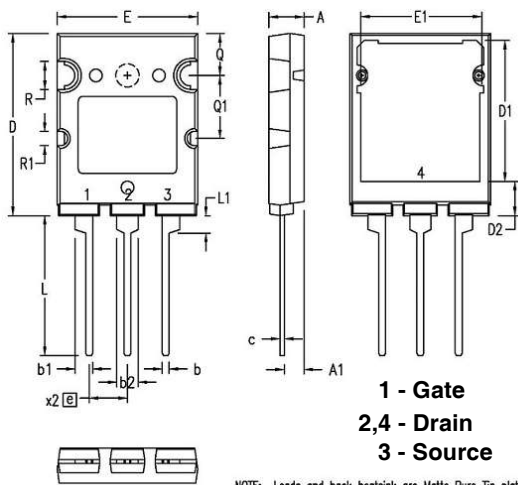


- 1 - Gate
- 2,4 - Drain
- 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S		.242 BSC		6.15 BSC

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)

### TO-264 Outline



- 1 - Gate
- 2,4 - Drain
- 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.30
A1	.102	.118	2.60	3.00
b	.035	.049	0.90	1.25
b1	.091	.106	2.30	2.70
b2	.110	.126	2.80	3.20
c	.020	.033	0.50	0.85
D	1.012	1.035	25.70	26.30
D1	.783	.799	19.90	20.30
D2	.185	.205	4.70	5.20
E	.776	.799	19.70	20.30
E1	.661	.677	16.80	17.20
e	.215 BSC		5.46 BSC	
L	.768	.807	19.50	20.50
L1	.091	.106	2.30	2.70
Q	.228	.244	5.80	6.20
Q1	.346	.362	8.80	9.20
øR	.150	.165	3.80	4.20
øR1	.071	.087	1.80	2.20

NOTE: Leads and back heatsink are Matte Pure Tin plated.



---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

---